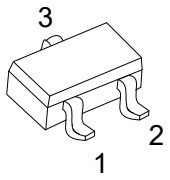
BSS139Z

Power MOSFET

N-CHANNEL LOGIC LEVEL ENHANCEMENT MODE



SOT-23-3
(JEDEC TO-236)

■ DESCRIPTION

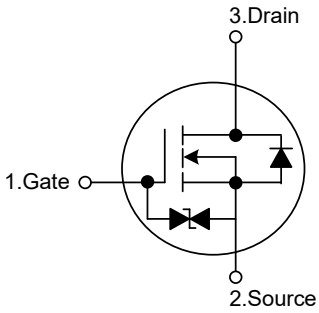
This device employs advanced MOSFET technology and features low gate charge while maintaining low on-resistance.

Optimized for switching applications, this device improves the overall efficiency of DC/DC converters and allows operation to higher switching frequencies.

■ FEATURES

* $R_{DS(ON)}$ ≤ 1.8 Ω @ V_{GS}=10 V, I_D=0.22A
  $R_{DS(ON)}$ ≤ 2.4 Ω @ V_{GS}=4.5V, I_D=0.22A
  $R_{DS(ON)}$ ≤ 6.5 Ω @ V_{GS}=2.5V, I_D=0.20A
* Low Capacitance
* Low Gate Charge
* Fast Switching Capability
* Avalanche Energy Specified

■ SYMBOL



■ ORDERING INFORMATION

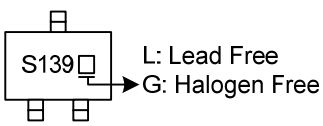
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BSS139ZL-AE2-R	BSS139ZG-AE2-R	SOT-23-3	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

BSS139ZG-AE2-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) AE2: SOT-23-3
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	50	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	DC	I_D	0.22	A
	Pulse		0.88	A
Peak Diode Recovery dv/dt		dv/dt	4.8	V/ns
Power Dissipation		P_D	225	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	556	°C/W

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

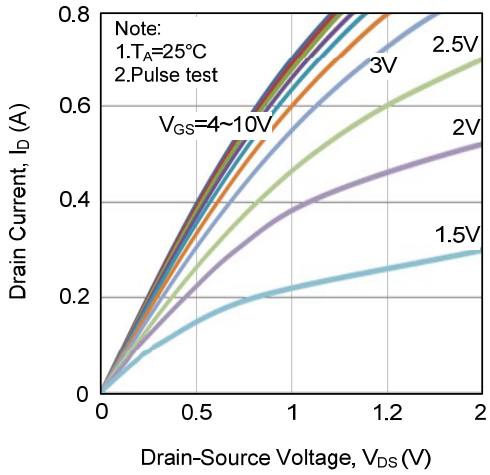
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	50			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=50V, V_{GS}=0V			1	μA
		V_{DS}=30V, V_{GS}=0V			0.5	μA
Gate–Body Leakage, Forward	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	uA
ON CHARACTERISTICS (Note)						
Gate-Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=1mA	0.5	0.9	1.5	V
Static Drain–Source On–Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=0.22A		1.3	1.8	Ω
		V_{GS}=4.5V, I_D=0.22A		1.5	2.4	Ω
		V_{GS}=2.5V, I_D=0.20A		2.2	6.5	Ω
On-State Drain Current	$I_{D(ON)}$	V_{GS}=10 V, V_{DS}=5V	0.2			A
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1MHz		16.7		pF
Output Capacitance	C_{OSS}			10.2		pF
Reverse Transfer Capacitance	C_{RSS}			4.5		pF
SWITCHING PARAMETERS (Note)						
Total Gate Charge	Q_G	V_{DS}=40V, V_{GS}=10V, I_D=0.22A		8.2		nC
Gate Source Charge	Q_{GS}			1.1		nC
Gate Drain Charge	Q_{GD}			0.3		nC
Turn-ON Delay Time	$t_{D(ON)}$	V_{DD}=30V, I_D=0.22A,V_{GS}=10V, R_G=6Ω		0.8		ns
Turn-ON Rise Time	t_R			16		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			6.4		ns
Turn-OFF Fall-Time	t_F			13		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Max. Diode Forward Current	I_S				0.22	A
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=0.44A		0.8	1.4	V
Reverse Recovery Time	t_{rr}	V_{GS}=0V, I_S=0.22A, d_I/d_t=100A/μs		18		ns
Reverse Recovery Charge	Q_{rr}			12		nC

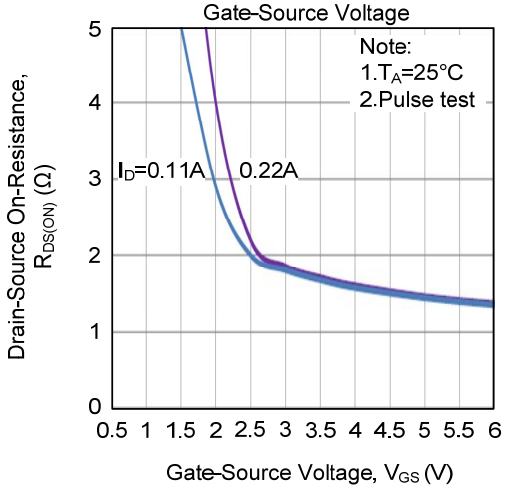
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TYPICAL CHARACTERISTICS

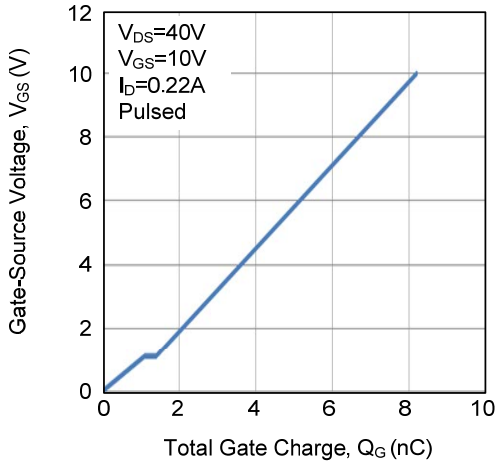
Drain Current vs. Drain-Source Voltage



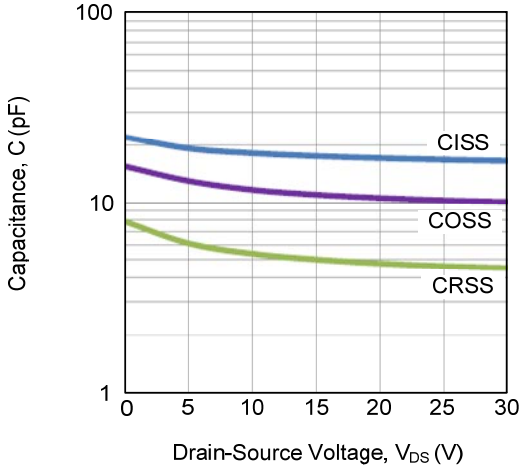
Drain-Source On-Resistance vs. Gate-Source Voltage



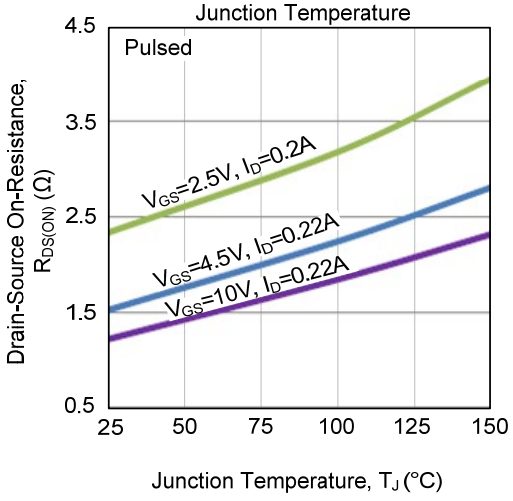
Gate Charge Characteristics



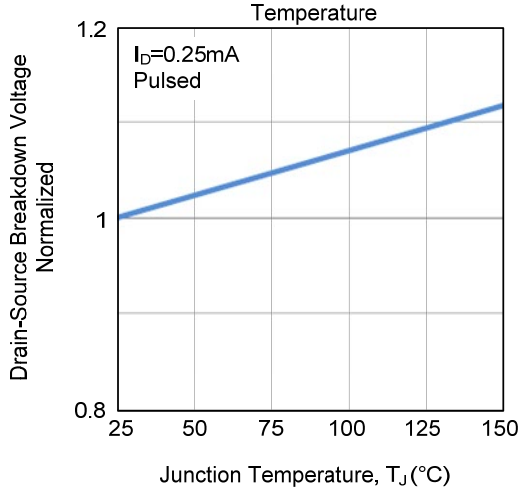
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

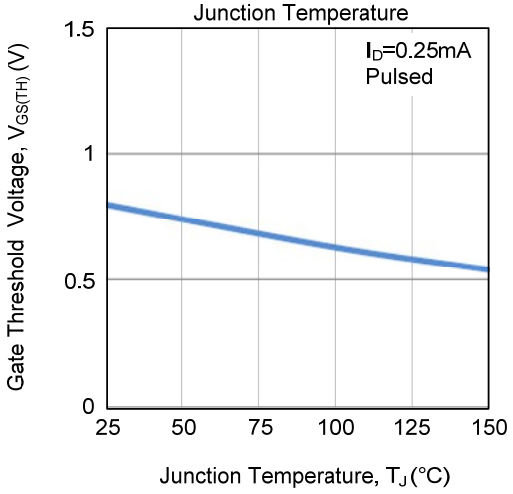


Breakdown Voltage vs. Junction Temperature

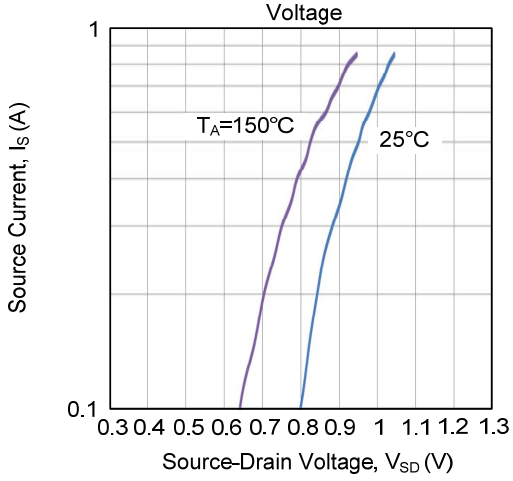


■ TYPICAL CHARACTERISTICS (Cont.)

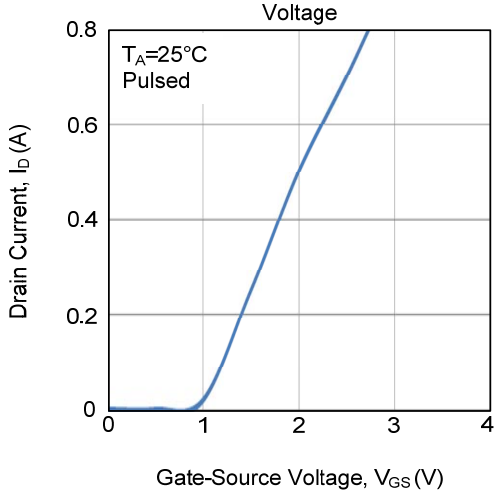
Gate Threshold Voltage vs. Junction Temperature



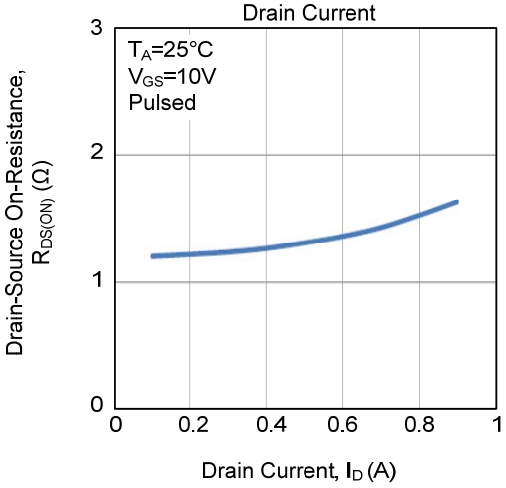
Source Current vs. Source-Drain Voltage



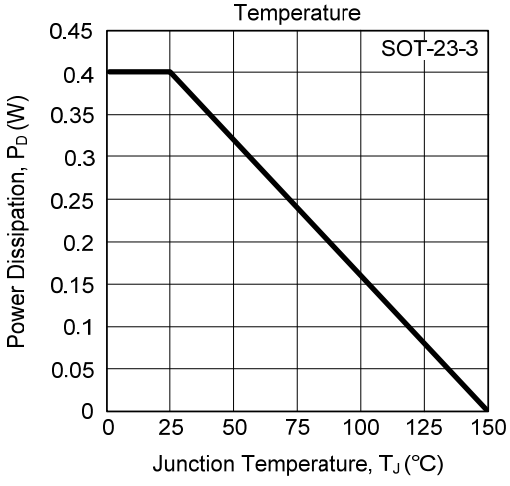
Drain Current vs. Gate-Source Voltage



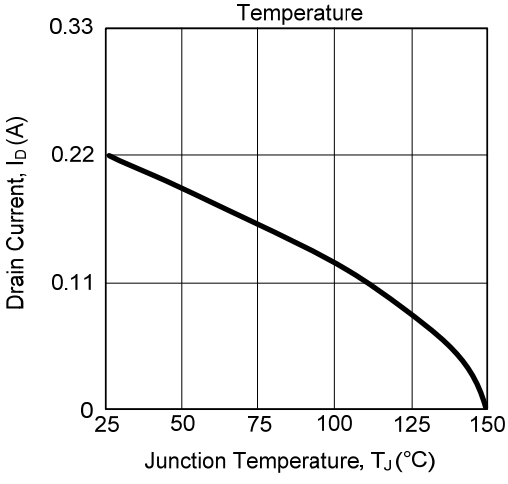
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)